

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity or Invertors

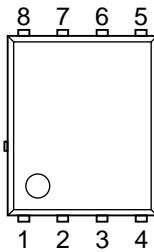
#### Pin Description

Pin	Description
1,2,3	Source(S)
4	Gate(G)
5,6,7,8	Drain(D)

#### Applications

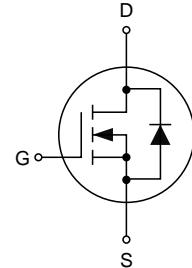
- Consumer electronic power supply Motor control
- Synchronous-rectification Isolated DC
- Synchronous-rectification applications

#### Simplified Outline



Top View  
PDFN5x6-8L

#### Symbol



#### Quick reference

- $B_V \geq 60V$
- $I_D \leq 130A$
- $R_{DS(ON)} \leq 3.0m\Omega$  @  $V_{GS} = 10V$  (Type:2.5 m $\Omega$ )

#### Package Marking and Ordering Information

Product Name	Package	Marking		Reel Size	Tape width	Quantity
KJ130N06G	PDFN5x6-8L	130N06	YWWXXX	-	-	5000

### 2. Absolute Maximum Ratings ( $T_J=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Min	Max	Unit
$V_{DS}$	Drain-Source Voltage	60	-	V
$V_{GS}$	Gate-Source Voltage	-	$\pm 20$	V
$I_D$ <sup>1</sup>	Drain Current	-	130	A
$I_{DM}$ <sup>2</sup>	Pulsed Drain Current	-	390	A
$P_{tot}$ <sup>3</sup>	Total Power Dissipation	-	140	W
$T_{stg}$	Storage Temperature	-55	150	°C
$T_J$	Junction Temperature	-	150	°C
$E_{AS}$ <sup>5</sup>	Single Pulsed Avalanche Energy	-	320	mJ
$R_{\theta JC}$	Thermal Resistance- Junction to Case	-	0.89	°C/W
$R_{\theta JA}$ <sup>4</sup>	Thermal Resistance- Junction to ambient	-	62	°C/W

### 3. Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}}=0\text{V}$ , $I_{\text{D}}=250\mu\text{A}$	60			V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=250\mu\text{A}$	1.0		2.5	V
$R_{\text{DS(ON)}}$	Drain-source on-state resistance	$V_{\text{GS}}=10\text{V}$ , $I_{\text{D}}=20\text{A}$		2.5	3.0	$\text{m}\Omega$
$R_{\text{DS(on)}}$	Drain-source on-state resistance	$V_{\text{GS}}=4.5\text{V}$ , $I_{\text{D}}=10\text{A}$		3.5	4.5	$\text{m}\Omega$
$I_{\text{GSS}}$	Gate-source leakage current	$V_{\text{GS}}=\pm 20\text{V}$			$\pm 100$	nA
$I_{\text{DSS}}$	Drain-source leakage current	$V_{\text{DS}}=60\text{V}$ , $V_{\text{GS}}=0\text{V}$			1	$\mu\text{A}$
$C_{\text{iss}}$	Input Capacitance	$V_{\text{GS}}=0\text{V}$ , $V_{\text{DS}}=25\text{V}$ , $f=100\text{kHz}$		5377		pF
$C_{\text{oss}}$	Output Capacitance			1666		pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			77.7		pF
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{GS}}=10\text{V}$ , $V_{\text{DS}}=30\text{V}$ , $R_{\text{G}}=2\Omega$ , $I_{\text{D}}=25\text{A}$		22.5		ns
$t_{\text{r}}$	Turn-on Rise Time			6.7		ns
$t_{\text{d(off)}}$	Turn-off Delay Time			80.3		ns
$t_{\text{f}}$	Turn-off Fall Time			26.8		ns
$Q_{\text{gs}}$	Gate-source charge	$I_{\text{D}}=25\text{A}$ , $V_{\text{DS}}=30\text{V}$ , $V_{\text{GS}}=10\text{V}$		10.7		nC
$Q_{\text{gd}}$	Gate-drain charge			10.9		nC
$V_{\text{plateau}}$	Gate plateau voltage			2.9		V
$I_{\text{s}}$	Diode forward current	$V_{\text{GS}} < V_{\text{th}}$ $I_{\text{s}}=20\text{A}$ , $V_{\text{GS}}=0\text{V}$			130	A
$I_{\text{SP}}$	Pulsed source current				390	A
$V_{\text{SD}}$	Diode forward voltage				1.3	V
$t_{\text{rr}}$	Reverse Recovery Time	$I_{\text{s}}=25\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		68.3		ns
$Q_{\text{rr}}$	Reverse Recovery Charge			73		nC
$I_{\text{rrm}}$	Peak reverse recovery current			1.9		A

Notes:

1. Calculated continuous current based on maximum allowable junction temperature.
2. Repetitive rating; pulse width limited by max. junction temperature.
3.  $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
4. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25^\circ\text{C}$ .
5.  $V_{DD}=50\text{V}$ ,  $R_{\text{G}}=25\Omega$ ,  $L=0.3\text{mH}$ , starting  $T_J=25^\circ\text{C}$ .

#### 4. Typical Characteristics

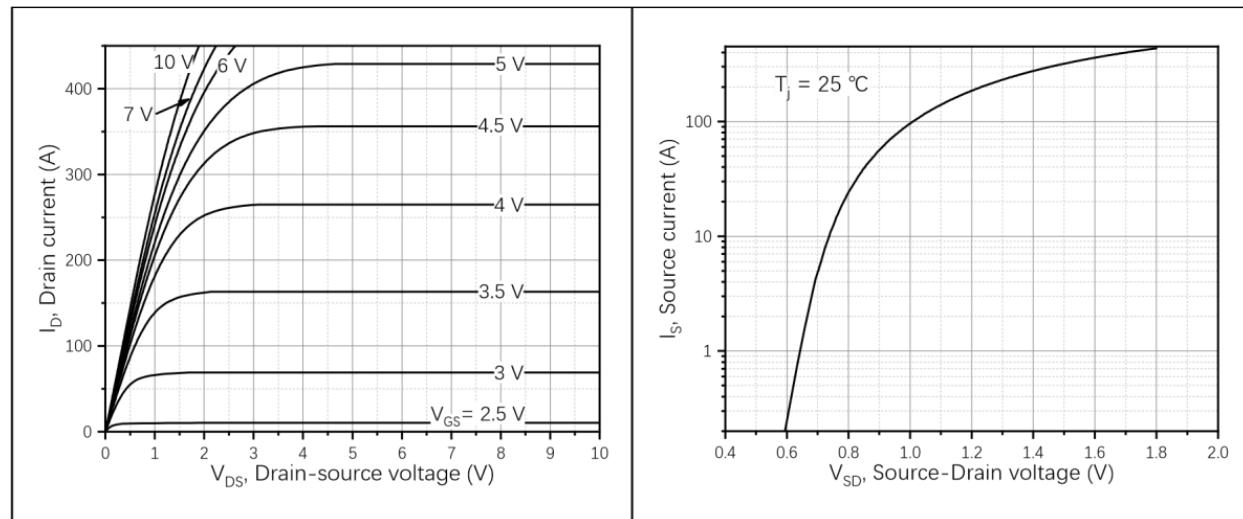


Figure 1, Typ. output characteristics

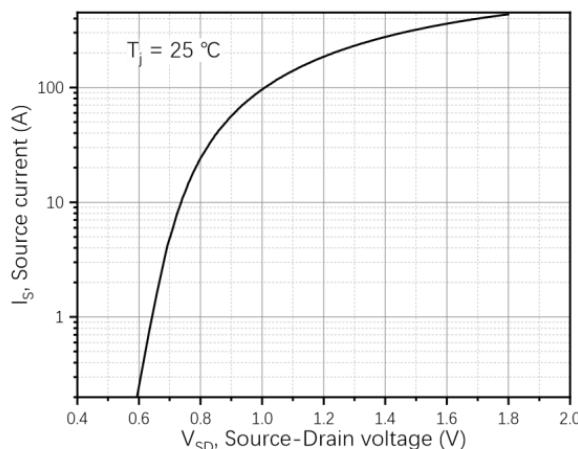


Figure 2, Typ. transfer characteristics

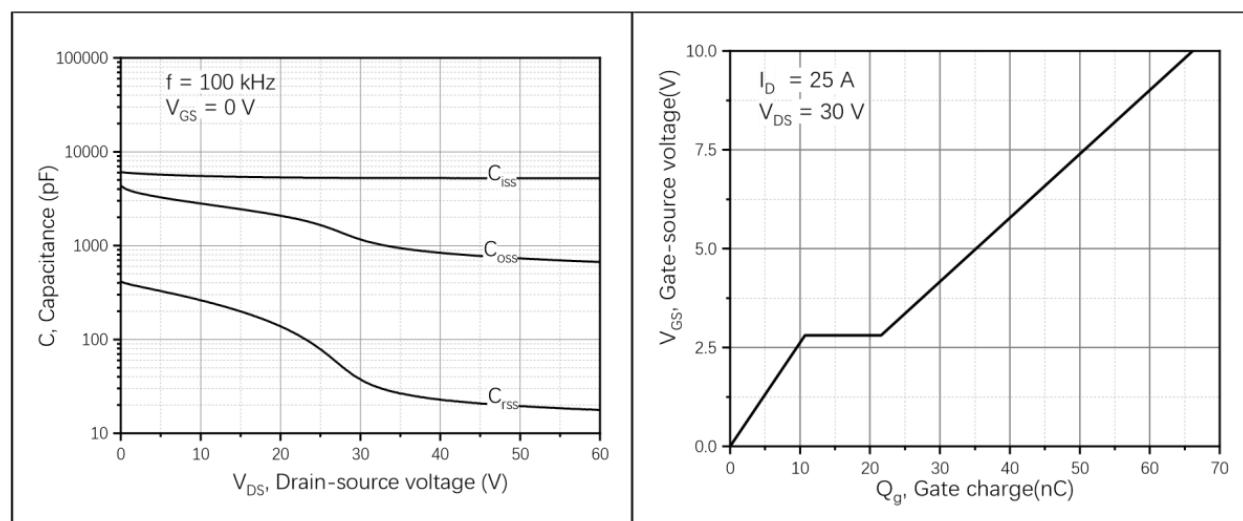


Figure 3, Typ. capacitances

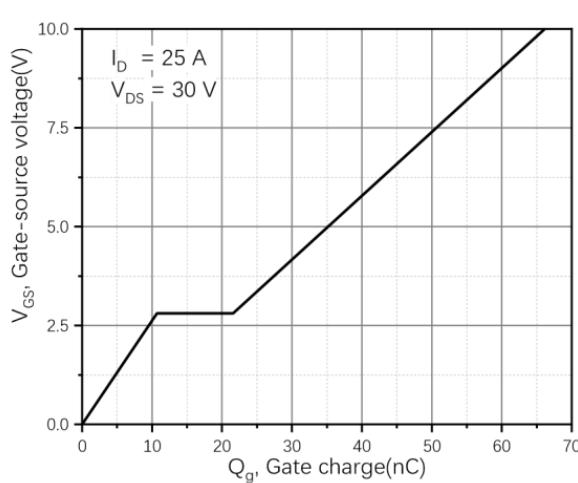


Figure 4, Typ. gate charge

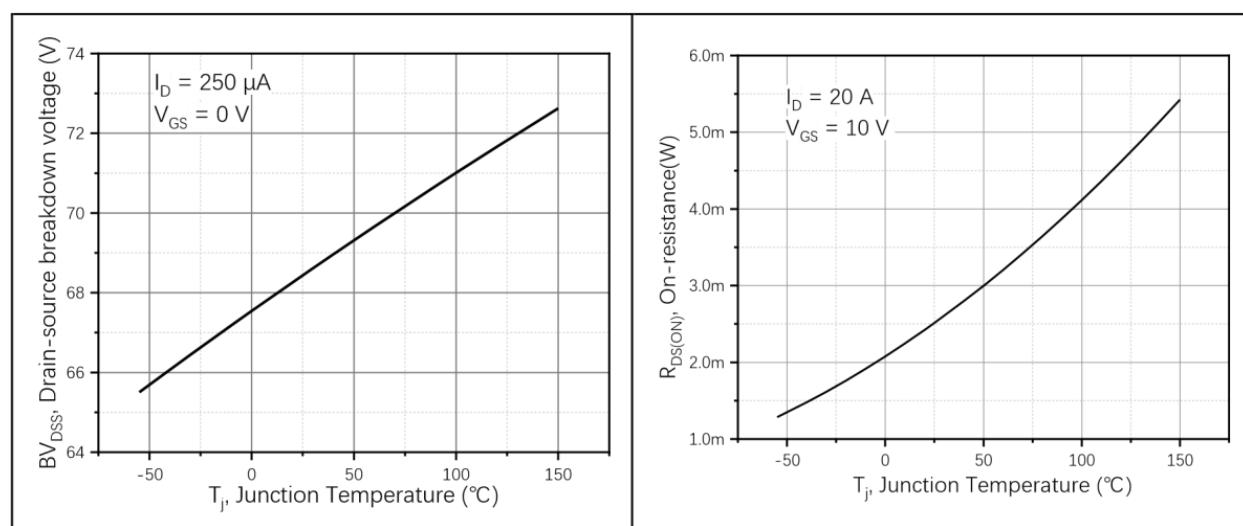


Figure 5, Drain-source breakdown voltage

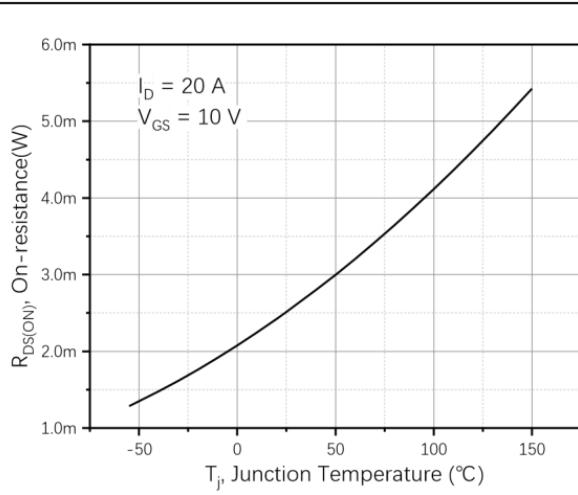


Figure 6, Drain-source on-state resistance

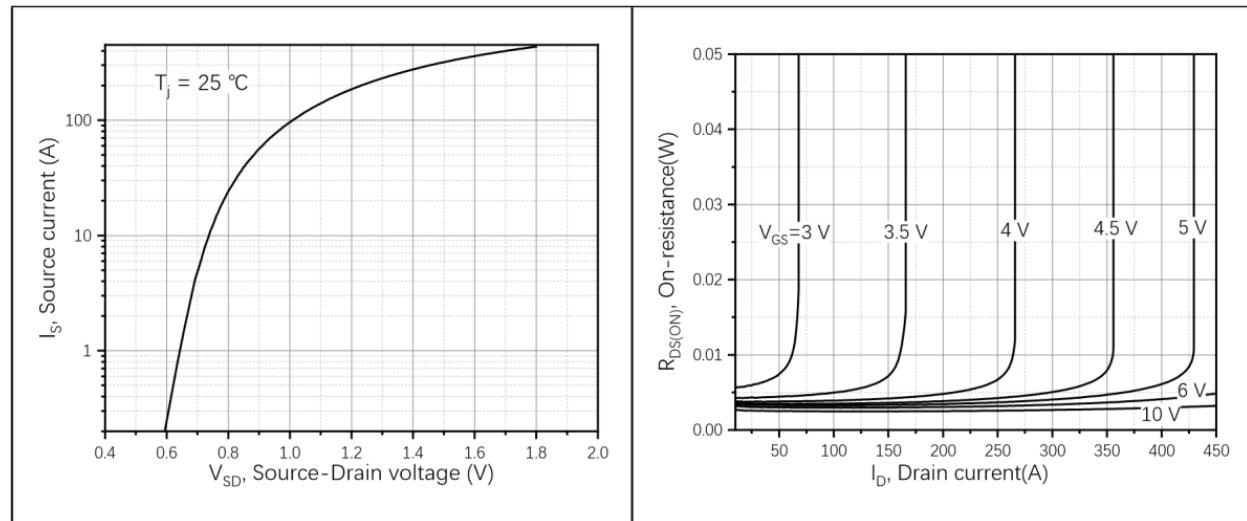


Figure 7, Forward characteristic of body diode

Figure 8, Drain-source on-state resistance

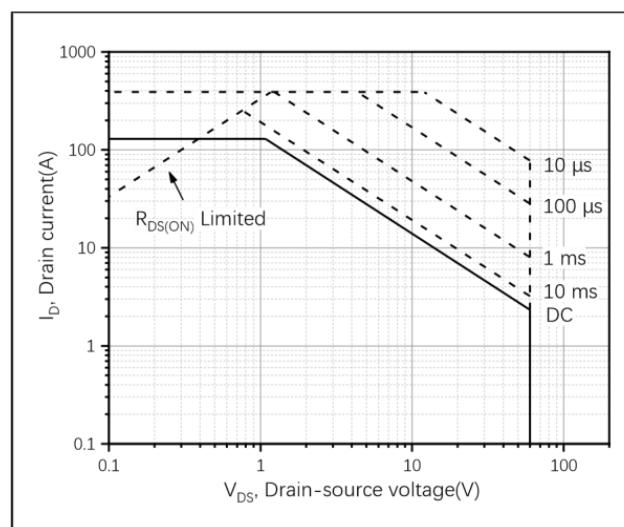


Figure 9, Safe operation area  $T_C=25^\circ\text{C}$

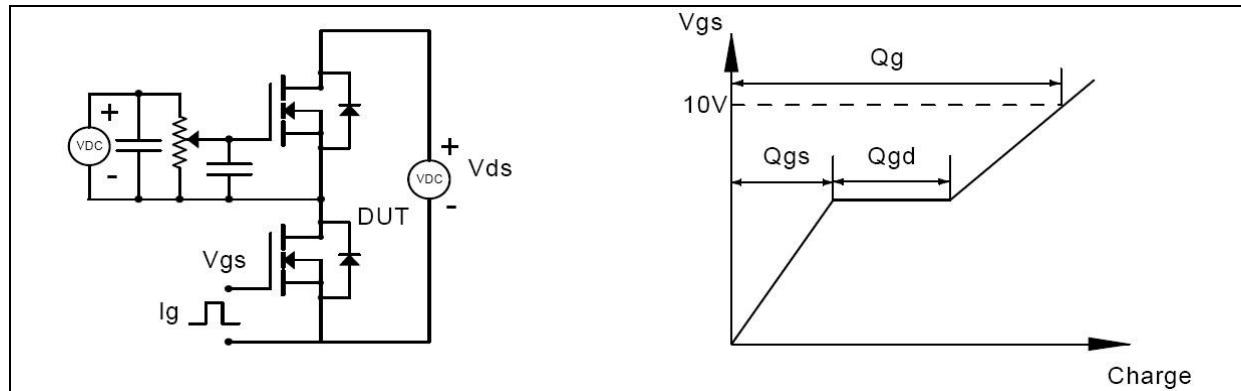


Figure 1, Gate charge test circuit & waveform

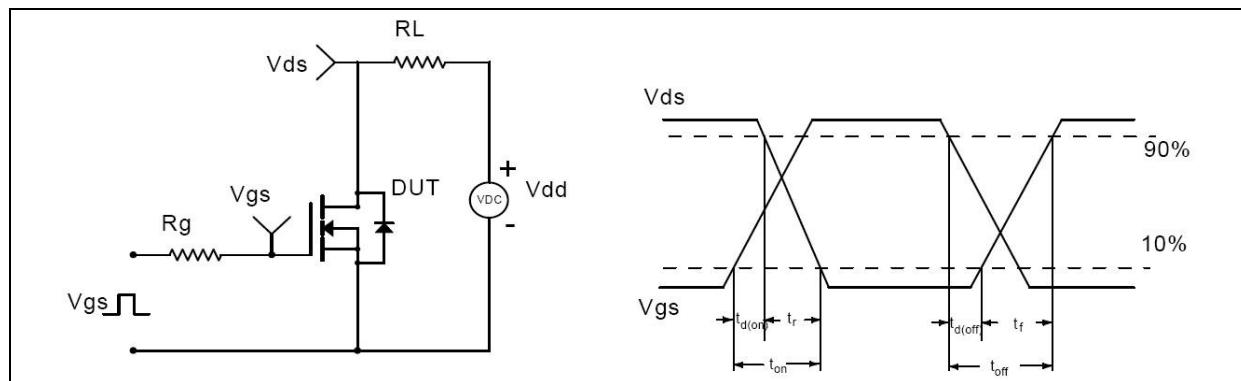


Figure 2, Switching time test circuit & waveforms

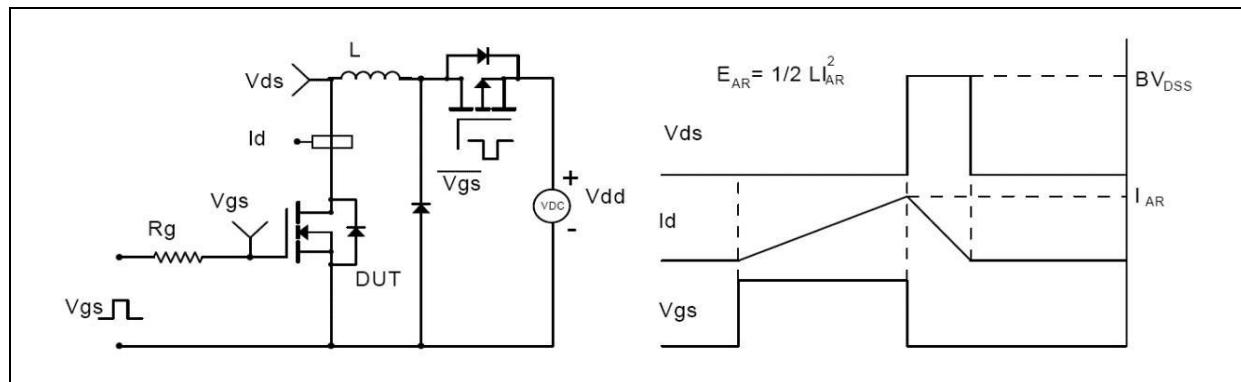


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

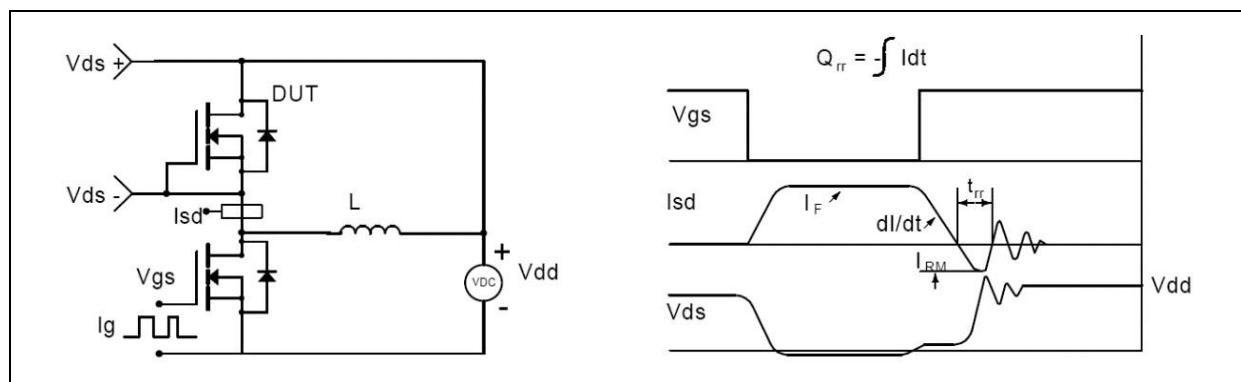
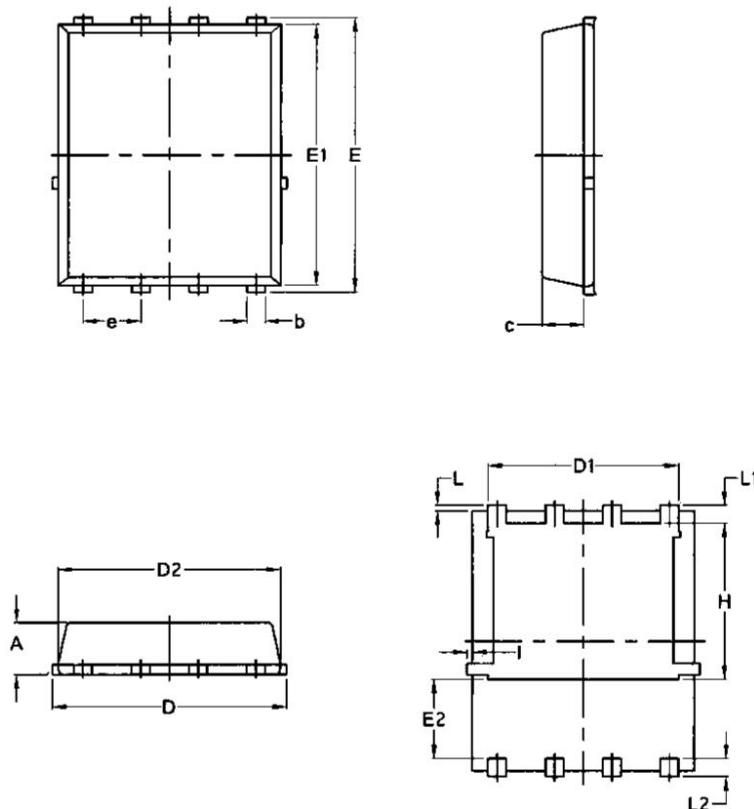


Figure 4, Diode reverse recovery test circuit & waveforms

## 5. Package Mechanical Data

PDFN5x6-8L Package



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070